DERWENT-ACC-NO:

1992-067414

DERWENT-WEEK:

199951

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TITLE:

Thin-film FET for memory - has source and

drain

electrodes buried in insulation film between

upper gate

electrode and film covering lower electrode

NoAbstract

Dwg 1/9

PATENT-ASSIGNEE: CASIO COMPUTER CO LTD [CASK]

PRIORITY-DATA: 1990JP-0092021 (April 9, 1990)

PATENT-FAMILY:

JP 03290970 A

JP 2969184 B2

PUB-NO

PUB-DATE

LANGUAGE

PAGES

MAIN-IPC

December 20, 1991

N/A

005

M/A

November 2, 1999

N/A

^^^

H01L 027/115

APPLICATION-DATA:

PUB-NO

APPL-DESCRIPTOR

APPL-NO

APPL-DATE

JP 03290970A

N/A

1990JP-0092021

April 9, 1990

JP 2969184B2

N/A

1990JP-0092021

April 9, 1990

JP 2969184B2

Previous Publ.

JP 3290970

N/A

INT-CL (IPC): HolL021/8247, HolL027/11, HolL027/115, HolL029/78

HO1L029/788 , H01L029/792

ABSTRACTED-PUB-NO: JP 2969184B

EQUIVALENT-ABSTRACTS:

Optical disk having a resin substrate has a trench on the periphery when the resin substrates are adhered to each other. A groove or pit for tracking is formed on a side of a resin substrate. A lst ceramics layer, a

recording
layer, 2nd ceramics layer and a reflection layer are laminated in order. The plates are adhered using epoxy gp. resin. A trench is formed at the periphery and a UV curing type resin is filled into the trench. The resin is cured and the periphery is cut.

ADVANTAGE - No change of mechanical characteristics at higher temp..

TITLE-TERMS: THIN FILM FET MEMORY SOURCE DRAIN ELECTRODE BURY INSULATE FILM

UPPER GATE ELECTRODE FILM COVER LOWER ELECTRODE NOABSTRACT

DERWENT-CLASS: U11 U12 U13 U14

EPI-CODES: U11-C18B5; U12-B03A; U12-D02A1; U12-Q; U13-C04B2; U14-A03B7; U14-H01A;

SECONDARY-ACC-NO:
Non-CPI Secondary Accession Numbers: N1992-050492